



DC COMPONENTS CO., LTD.

RECTIFIER SPECIALISTS

BAV101
THRU
BAV103

TECHNICAL SPECIFICATIONS OF SURFACE MOUNT SWITCHING DIODES

VOLTAGE RANGE - 100 to 200 Volts

CURRENT - 0.2 Ampere

FEATURES

- * Silicon epitaxial planar diodes
- * Low power loss, high efficiency
- * Low leakage
- * Low forward voltage
- * High current capability
- * High reliability

MECHANICAL DATA

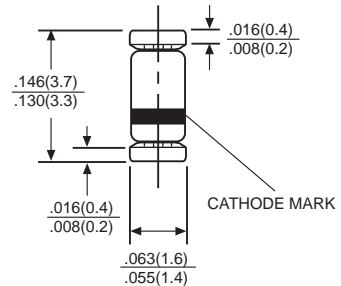
- * Case: Glass sealed case
- * Terminals: Solder plated, solderable per MIL-STD-750E, Method 2026 guaranteed
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.05 grams Approx.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.



Mini Melf(DL-35)



Dimensions in inches and (millimeters)

	SYMBOL	BAV101	BAV102	BAV103	UNITS
Maximum Reverse Voltage	VR	100	150	200	V
Maximum Recurrent Peak Reverse Voltage	VRRM	120	200	250	V
Maximum Average Rectified Current	Io	200			mA
Peak Forward Surge Current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	1.0			A
Maximum Power Dissipation Tamb=25°C	Ptot	300			mW
Maximum Forward Voltage (@IF=100mA)	VF	1.0			V
Maximum Reverse Current (@VR=VR Max)	IR	0.1			µA
Maximum Reverse Recovery Time(Note 1)	trr	75			nS
Typical Junction Capacitance(Note 2)	CJ	1.5			pF
Typical Thermal Resistance	RθJA	357			°C/W
Operating and Storage Temperature Range	TJ,TSTG	-55 to +125			°C

Note: 1. Test Conditions: IF=IR=10mA, RL=100Ω, VR=6V to IRR=1mA, RL=100Ω

2. Measured at 1MHz and VR=0

RATING AND CHARACTERISTIC CURVES (BAV101 THRU BAV103)

FIG.1 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

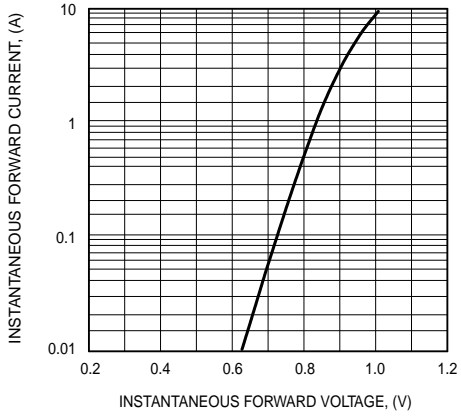


FIG.2 - TYPICAL REVERSE CHARACTERISTICS

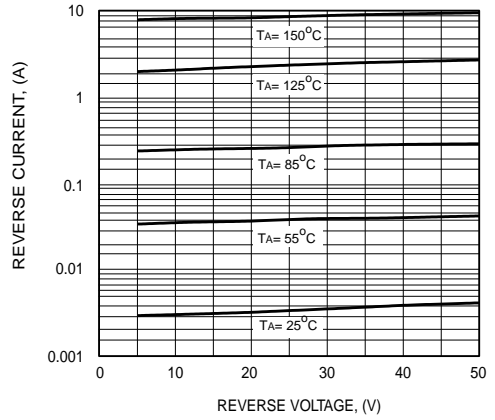


FIG.3 - TYPICAL JUNCTION CAPACITANCE

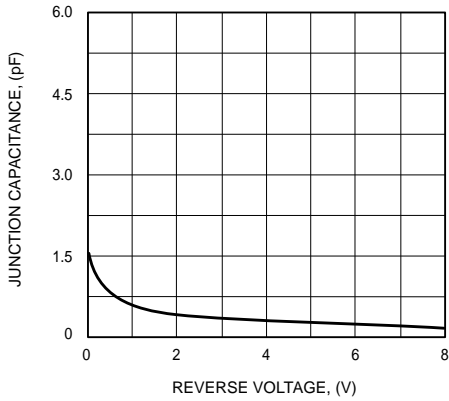


FIG.4 - RECTIFICATION EFFICIENCY MEASUREMENT CIRCUIT

